

58STS8205E-VB Datasheet

Dual N-Channel MOSFET

PRODUCT SUMMARY				
V _{DS} (V)	$R_{DS(on)}$ (Ω)	I _D (A)		
20	$0.024 \text{ at V}_{GS} = 4.5 \text{ V}$	6.0		
	0.028 at V _{GS} = 2.5 V	5.0		

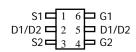
FEATURES

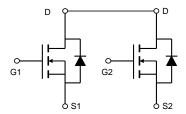
- Halogen-free Option Available
- TrenchFET $^{\text{®}}$ Power MOSFETs 100 % R_{g} Tested
- Compliant to RoHS Directive 2002/95/EC





TSOP6 **Top View**





ABSOLUTE MAXIMUM RATINGS T _A = 25 °C, unless otherwise noted						
Parameter		Symbol	10 s	Steady State	Unit	
Drain-Source Voltage		V _{DS}	20		V	
Gate-Source Voltage		V _{GS}	± 12			
Continuous Proin Current /T 450 °C\8	T _A = 25 °C	I _D	6.0	5.2		
Continuous Drain Current (T _J = 150 °C) ^a	T _A = 70 °C		4.8	4.2	٨	
Pulsed Drain Current		I _{DM}	30		А	
Continuous Source Current (Diode Conduction) ^a	I _S	1.5	1.0			
Manianum Danier Discipation	T _A = 25 °C	P _D	1.5	1.0	W	
Maximum Power Dissipation ^a	T _A = 70 °C] '`D	0.96	0.64	V V	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 150		°C	

THERMAL RESISTANCE RATINGS						
Parameter	Symbol	Тур.	Max.	Unit		
Mariana haria ta Arkinda	t ≤ 10 s	R_{thJA}	72	83	°C/W	
Maximum Junction-to-Ambient ^a	Steady State		100	120		
Maximum Junction-to-Foot (Drain)	Steady State	R_{thJF}	55	70		

a. Surface Mounted on FR4 board, $t \le 10 \text{ s.}$

^{*} Pb containing terminations are not RoHS compliant, exemptions may apply.



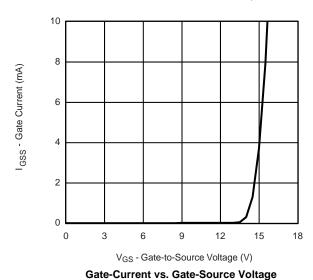
SPECIFICATIONS T _J = 25 °C, unless otherwise noted								
Parameter	Symbol	Test Conditions Min.		Typ. ^a	Max.	Unit		
Static								
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	0.5		1.5	V		
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 4.5 \text{ V}$			± 200	nA		
Zara Cata Valtaga Drain Current		V _{DS} = 20 V, V _{GS} = 0 V			1	μA		
Zero Gate Voltage Drain Current	I _{DSS}	$V_{DS} = 20 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 70 ^{\circ}\text{C}$	$_{OS} = 20 \text{ V}, \text{ V}_{GS} = 0 \text{ V}, \text{ T}_{J} = 70 \text{ °C}$					
On-State Drain Current ^b	I _{D(on)}	$V_{DS} \le 5 \text{ V}, V_{GS} = 4.5 \text{ V}$	30			Α		
5 · 6 · 6 · 6 · 6 · 6	R _{DS(on)}	$V_{GS} = 4.5 \text{ V}, I_D = 5.5 \text{ A}$		0.024		0		
Drain-Source On-State Resistance ^b		$V_{GS} = 2.5 \text{ V}, I_D = 3.5 \text{ A}$		0.028		Ω		
Forward Transconductance ^b	9 _{fs}	$V_{DS} = 10 \text{ V}, I_{D} = 5.5 \text{ A}$		30		S		
Diode Forward Voltage ^b	V_{SD}	I _S = 1.5 A, V _{GS} = 0 V		0.71	1.2	V		
Dynamic ^a								
Total Gate Charge	Q_g			12	18			
Gate-Source Charge	Q_{gs}	$V_{DS} = 10 \text{ V}, V_{GS} = 4.5 \text{ V}, I_{D} = 5.5 \text{ A}$		2.2		nC		
Gate-Drain Charge	Q_{gd}			3.6				
Turn-On Delay Time	t _{d(on)}			245	365			
Rise Time	t _r	V_{DD} = 10 V, R_L = 10 Ω		330	495			
Turn-Off Delay Time	t _{d(off)}	$I_D\cong$ 1 A, V_{GEN} = 4.5 V, R_G = 6 Ω		860	1300	ns		
Fall Time	t _f			510	765			

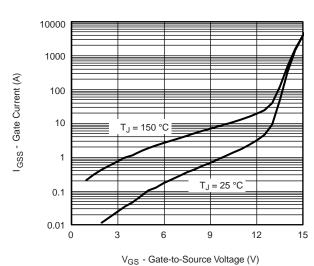
Notes:

- a. For design aid only; not subject to production testing.
- b. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

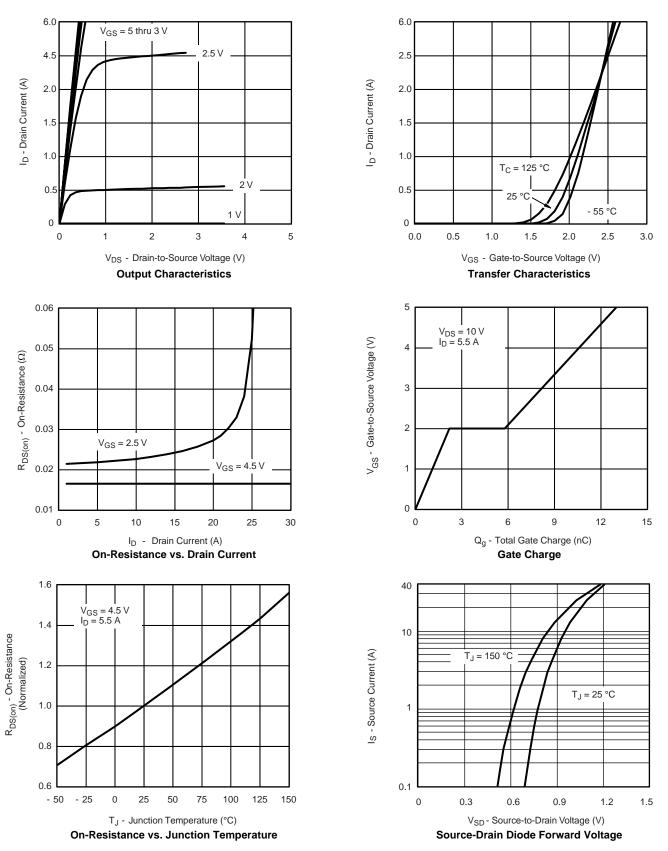




Gate Current vs. Gate-Source Voltage

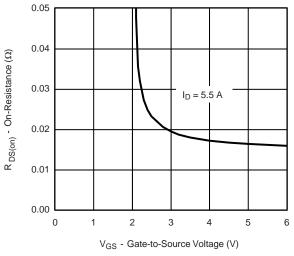


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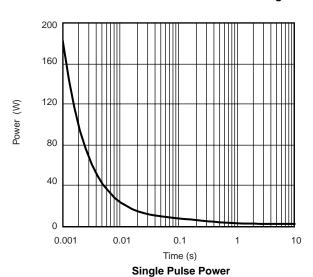




TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



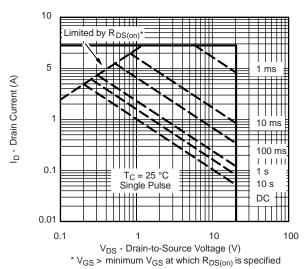
On-Resistance vs. Gate-to-Source Voltage

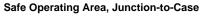


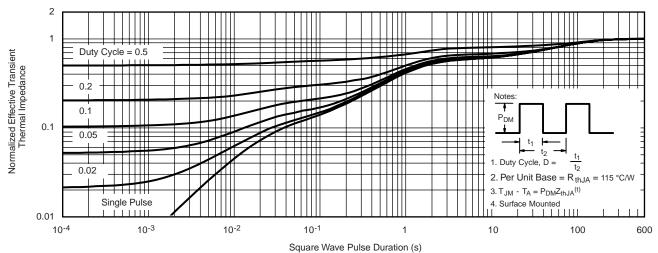
I_D = 250 μA 0.2 V_{GS(th)} Variance (V) 0.0 - 0.2 - 0.4 - 0.6 0 - 50 - 25 25 50 75 100 125 150

0.4





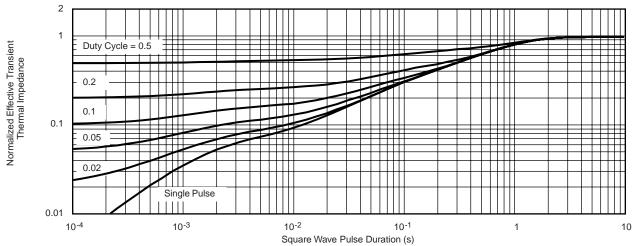




Normalized Thermal Transient Impedance, Junction-to-Ambient



TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

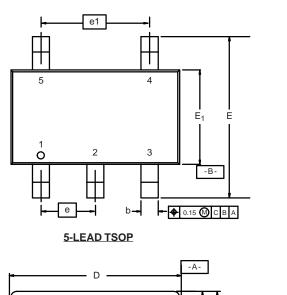


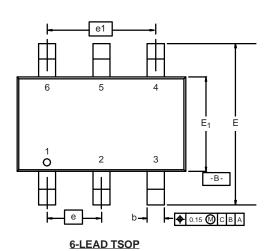
Normalized Thermal Transient Impedance, Junction-to-Foot



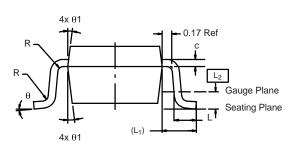
TSOP: 5/6-LEAD

JEDEC Part Number: MO-193C





A₂ A Seating Plane **a** 0.08 C -C- A₁

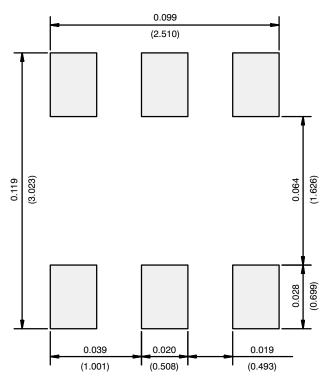


	MILLIMETERS			ı	NCHES		
Dim	Min	Nom	Max	Min	Nom	Max	
Α	0.91	-	1.10	0.036	-	0.043	
A ₁	0.01	-	0.10	0.0004	-	0.004	
A ₂	0.90	-	1.00	0.035	0.038	0.039	
b	0.30	0.32	0.45	0.012	0.013	0.018	
С	0.10	0.15	0.20	0.004	0.006	0.008	
D	2.95	3.05	3.10	0.116	0.120	0.122	
E	2.70	2.85	2.98	0.106	0.112	0.117	
E ₁	1.55	1.65	1.70	0.061	0.065	0.067	
е		0.95 BSC		0.0374 BSC			
e ₁	1.80	1.90	2.00	0.071	0.079		
L	0.32	-	0.50	0.012	-	0.020	
L ₁	0.60 Ref			0.024 Ref			
L ₂	0.25 BSC			0.010 BSC			
R	0.10	-	-	0.004	-	-	
θ	0°	4°	8°	0°	4°	8°	
θ_1		7° Nom		7° Nom			
ECN: C-06593-Rev. I, 18-Dec-06 DWG: 5540							

6



RECOMMENDED MINIMUM PADS FOR TSOP-6



Recommended Minimum Pads Dimensions in Inches/(mm)



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